

Internation oplication No PCT/JP 03/15200

A. CLASSIFICATION OF SUBJECT MATTER
IPC 7 H01L21/203 C30B23/02

C30B29/40

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols) IPC 7 C30B H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, PAJ, WPI Data, INSPEC

Category °	Citation of document, with Indication, where appropriate, of the relevant passages	Relevant to claim No.
X Y	MAYER M ET AL: "Reactive MBE of group III nitrides: high-quality homoepitaxial GaN and ultra-violet light-emitting diodes" JOURNAL OF CRYSTAL GROWTH, NORTH-HOLLAND PUBLISHING CO. AMSTERDAM, NL, vol. 201-202, May 1999 (1999-05), pages 318-322, XP004175132 ISSN: 0022-0248 cited in the application 2. Experimental procedure, 4. Ultra-violet light emitting diodes	1-7, 13-23 8-12
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X Further documents are listed in the continuation of box C.	Patent family members are listed in annex.
Special categories of cited documents: 'A' document defining the general state of the art which is not considered to be of particular relevance 'E' earlier document but published on or after the International filing date 'L' document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) 'O' document referring to an oral disclosure, use, exhibition or other means 'P' document published prior to the international filing date but later than the priority date claimed	"T" later document published after the International filing date or priority date and not in conflict with the application but clied to understand the principle or theory underlying the invention "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art. "&" document member of the same patent family
26 February 2004	Date of mailing of the international search report 09/03/2004
Name and mailing address of the ISA European Patent Office, P.B. 5818 Patentlaan 2 NL – 2280 HV Rijswijk Tel. (+31–70) 340–2040, Tx. 31 651 epo ni, Fax: (+31–70) 340–3016	Authorized officer Mauger, J



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Category •	ation) DOCUMENTS CONSIDERED TO BE RELEVANT Citation of document, with Indication, where appropriate, of the relevant passages	Indiana da da da
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X	MAYER M ET AL: "Device performance of ultra-violet emitting diodes grown by MBE" JOURNAL OF CRYSTAL GROWTH, NORTH-HOLLAND PUBLISHING, AMSTERDAM, NL, vol. 189-190, 15 June 1998 (1998-06-15), pages 782-785, XP004148622 ISSN: 0022-0248	1-6, 13-23
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X	ABERNATHY C R ET AL: "Growth of group III nitrides by metalorganic molecular beam epitaxy" JOURNAL OF CRYSTAL GROWTH, NORTH-HOLLAND PUBLISHING CO. AMSTERDAM, NL, vol. 178, no. 1-2, 1 June 1997 (1997-06-01), pages 74-86, XP004084976 ISSN: 0022-0248 4. Doping	1,2, 21-23
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Y	EP 1 164 210 A (SHARP KK) 19 December 2001 (2001-12-19) cited in the application paragraph '0041! - paragraph '0058!; claims; figure 1 paragraph '0013!	7-12
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Information on patent family members

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